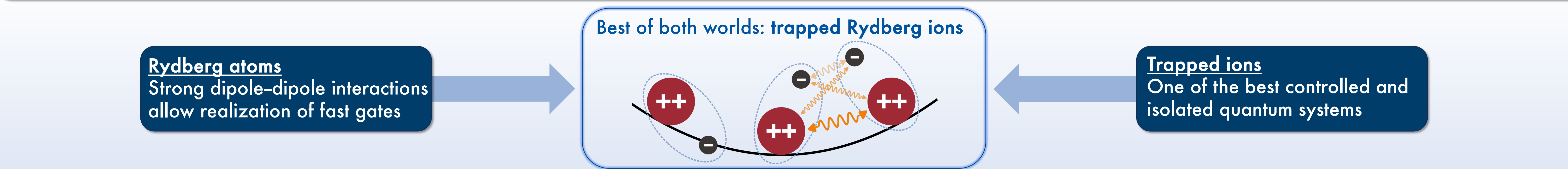


Quantum Information Processing with Trapped Rydberg Ions

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ABSTRACT
Combining the strong, long-range interactions of cold Rydberg atoms with the controllability of trapped ions, trapped Rydberg ions provide a promising platform for scalable quantum information processing. As demonstrated in a breakthrough experiment [1], microwave dressing of Rydberg states induces permanent rotating dipole moments leading to strong interactions between highly excited ions. Due to the separation of timescales, the fast electronic dynamics of Rydberg ions decouple from the slower motional modes of the linear Coulomb crystal, which typically mediate entangling gates in ground-state ion systems. Therefore, Rydberg ions enable significantly faster gate operations. We demonstrate how the unique properties of trapped Rydberg ions can be exploited to realize fast and high-fidelity entangling gates, along with the associated challenges and strategies to overcome them. Different types of gate protocols for two- and three-qubit entangling gates with trapped Rydberg ions are presented and sources of infidelity are analyzed.



RYDBERG PHYSICS

Binding energy $E = -\frac{Z^2 E_{\text{Ryd}}}{(n - \delta_l)^2}$

quantum defect

Property	n -scaling	Z -scaling
Energy levels E_n	n^{-2}	Z^2
Level spacing ΔE_n	n^{-3}	Z^2
Radius $\langle r \rangle$	n^2	Z^{-1}
Dipole moment adjacent states d	n^2	Z^{-1}
Polarizability α	n^7	Z^{-4}
Radiative lifetime τ	n^3	Z^{-4}
Dipole-dipole interaction $C_3, V_{dd} \sim R^{-3}$	n^4	Z^{-2}
Van der Waals interaction $C_6, V_{vdW} \sim R^{-6}$	n^{11}	Z^{-6}

	Sodium	Hydrogen
8p	8d	8f
7p	7d	7f
6p	6d	6f
5p	5d	5f
4p	4d	4f
3p	3d	3f
2p	2d	2f
1p	1d	1f

Electron position probability

large quantum defect

small quantum defect

r/a_0

MICROWAVE DRESSING

Dipole-dipole interaction $V_{ij} = \frac{1}{4\pi\epsilon_0} \frac{\mathbf{d}_i \cdot \mathbf{d}_j - 3(\mathbf{n}_{ij} \cdot \mathbf{d}_i)(\mathbf{n}_{ij} \cdot \mathbf{d}_j)}{|\mathbf{R}_{ij}|^3}$

$\mathbf{n}_{ij} = \frac{\mathbf{R}_{ij}}{|\mathbf{R}_{ij}|}$

→ Without MW, no permanent dipole moments: $\mathbf{d}_i = \mathbf{d}_j = 0$

→ V_{ij} has no first order effect

→ Second order: vdW $\sim n^{11} R^{-6} Z^{-6} \sim \text{kHz}$

- Principal quantum number n is limited due to trap ionisation

Dressed states: $|D_{\pm}\rangle_{\text{lab}} \sim |n, s\rangle \mp e^{-i\omega_{\text{MW}} t} |n, p\rangle \sim |n, s\rangle \mp e^{-i\omega_{\text{MW}} t} |n, p\rangle$

Interacting rotating dipole moments

$^{88}\text{Sr}^+$: $R_{ij} = 2.3 \mu\text{m}$, $n = 46$
→ $V_{ij} \approx 2\pi \times 25.8 \text{ MHz}$

B field and trap axis

Electric dipole

Microwave electric field

Time

Zhang et al. Nature 580 (2020)

PULSE OPTIMIZATION

Hamiltonian

$$H = \sum_{i,\pm} \left[\left(\Delta_L \pm \frac{\Omega_{\text{MW}}}{2} - \frac{i}{2} \gamma_R \right) |D_{\pm}\rangle \langle D_{\pm}|_i + \frac{\Omega_L}{2\sqrt{2}} (|1\rangle \langle D_{\pm}|_i + \text{H.c.}) \right] + \sum_{i \neq j} \frac{V_{ij}}{4} [\sigma_{z,i}^D \sigma_{z,j}^D + \sigma_{y,i}^D \sigma_{y,j}^D]$$

Pulses $\Omega_L(t) = \Omega_0 \sin^2\left(\frac{\pi t}{\tau}\right)$

$\Delta_L(t) = \delta_0 - \Delta_0 \sin^2\left(\frac{\pi t}{\tau}\right)$

optimization parameters

Optimization

We optimize the pulse parameters to yield the highest fidelity $\mathcal{F} = |\langle \Psi_I | U_T U(\tau) | \Psi_I \rangle|^2$ with $|\Psi_I\rangle = |+\rangle^{\otimes N}$

Infidelity caused by decay $\bar{p}_{\text{int}} \approx 1 - \left| 1 - \frac{\gamma_R}{2} \int_0^\tau dt \sum_{i,\pm} p_{\pm}^{(i)} \right|^2$, where $p_{\pm}^{(i)}$ is the population of $|D_{\pm}\rangle_i$

$U_T = \text{CZ}$
 $N = 2$

$U_T = \text{CCZ}$
 $N = 3$

RESULTS: IMPLEMENTING CCZ GATES

$\text{CCZ} : |abc\rangle \rightarrow (-1)^{abc} |abc\rangle, (a, b, c) \in \{0, 1\}^3$

Parameters	
$V_{12} = V_{23} = V$	$2\pi \times 25 \text{ MHz}$
Ω_{MW}	$2\pi \times 500 \text{ MHz}$
Ω_0	$2\pi \times [0, 100] \text{ MHz}$
δ_0	$2\pi \times [0, 250] \text{ MHz}$
Δ_0	$2\pi \times [-250, 250] \text{ MHz}$

CCZ gate with and without Rydberg decay

Main source of infidelity: population loss $\bar{p}_{\text{int}}$ due to decay and the phase error in $\varphi_{101}^{\text{ent}}$

Small τ or with decay
The time spent in the Rydberg states is reduced to minimize the error in $\varphi_{101}^{\text{ent}}$ and population loss caused by decay.

Large τ and without decay
The time spent in the Rydberg states is sufficient to accumulate all the desired phases. Since there is no population loss due to decay, high fidelities >99% are reached.

RESULTS: IMPLEMENTING CZ GATES

$\text{CZ} : |ab\rangle \rightarrow (-1)^{ab} |ab\rangle, (a, b) \in \{0, 1\}^2$

	Conservative	Optimistic
$V_{12} = V$	$2\pi \times 10 \text{ MHz}$	$2\pi \times 25 \text{ MHz}$
Ω_{MW}	$2\pi \times 100 \text{ MHz}$	$2\pi \times 250 \text{ MHz}$
Ω_0	$2\pi \times [0, 10] \text{ MHz}$	$2\pi \times [0, 100] \text{ MHz}$
δ_0	$2\pi \times [0, 100] \text{ MHz}$	$2\pi \times [0, 250] \text{ MHz}$
Δ_0	$2\pi \times [-100, 100] \text{ MHz}$	$2\pi \times [-250, 250] \text{ MHz}$

CZ gate without noise

CZ gate with Rydberg decay
 $\tau_R = 7.8 \mu\text{s}$, $\gamma_R = 0.128 \text{ MHz}$

200 ns gate with >99% Fidelity